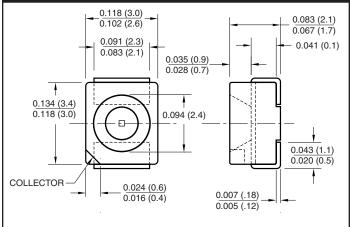


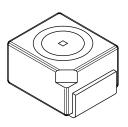
QSB320 SURFACE MOUNT SILICON INFRARED PHOTOTRANSISTOR

PACKAGE DIMENSIONS



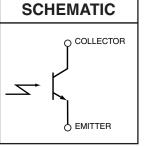
NOTES:

- 1. Dimensions for all drawings are in inches (millimeters).
- 2. Tolerance of \pm .010 (.25) on all non nominal dimensions unless otherwise specified.



FEATURES

- Surface Mount PLCC-2 Package
- Wide Reception Angle, 120°
- High Sensitivity
- Phototransistor Output
- Matched Emitter: QEB421



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}C$ unless otherwise specified)							
Parameter	Symbol	Rating	Unit				
Operating Temperature	T _{OPR}	-55 to +100	°C				
Storage Temperature	T _{STG}	-55 to +100	°C				
Soldering Temperature (Flow) ^(2,3)	T _{SOL-F}	260 for 10 sec	°C				
Collector Emitter Voltage	V _{CE}	35	V				
Emitter Collector Voltage	V _{EC}	5	V				
Collector Current	Ι _C	15	mA				
Power Dissipation ⁽¹⁾	PD	D 165					

NOTES

- 1. Derate power dissipation linearly 2.2 mW/°C above 25°C.
- 2. RMA flux is recommended.
- 3. Methanol or isopropyl alcohols are recommended as cleaning agents.
- 4. $\lambda = 940$ nm.

ELECTRICAL / OPTICAL CHARACTERISTICS (TA =25°C)

PARAMETER	TEST CONDITIONS	SYMBOL	MIN	ТҮР	MAX	UNITS
Peak Sensitivity Wavelength		λ_{PS}	—	880		nm
Wavelength Sensitivity Range		λ_{SR}	400	—	1000	nm
Reception Angle		θ	_	120	_	Deg.
Collector Emitter Dark Current	$V_{CE} = 25 \text{ V}, \text{ E}_{e} = 0$	I _D	_	_	200	nA
Collector Emitter Breakdown	$I_{\rm C} = 1 \rm{mA}$	BV _{CEO}	30	_	_	V
Emitter Collector Breakdown	I _E = 100 μA	BV_{ECO}	5	_	_	V
On-State Collector Current	$E_e = 0.1 \text{ mW/cm}^{2(4)}, V_{CE} = 5 \text{ V}$	I _{C (ON)}	16	_	_	μA
Saturation Voltage	$E_e = 0.5 \text{ mW/cm}^{2(4)}, \ I_C = 0.05 \text{ mA}$	V _{CE (SAT)}	—	—	0.3	V
Rise Time	V_{CC} = 5 V, R_L = 100 Ω	t _r		8		μs
Fall Time	$I_{\rm C} = 1 \rm{mA}$	t _f	—	8	_	μs



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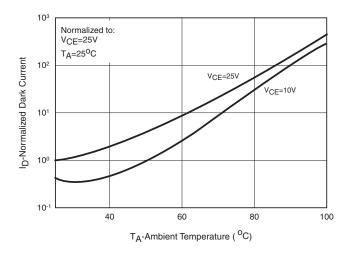
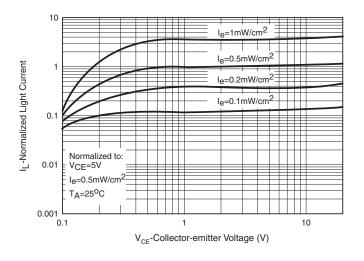


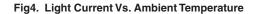
Fig.1 Dark Current Vs. Ambient Temperature

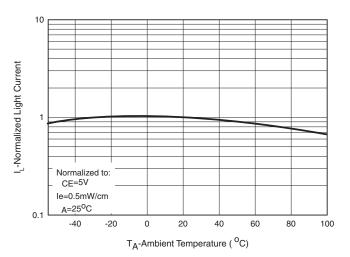
Fig.3 Light Current Vs. Collector to Emitter Voltage



 $(u) \\ (u) \\ (u)$

Fig.2 Dark Current Vs. Collector Emitter Voltage







QSB320 SURFACE MOUNT SILICON INFRARED PHOTOTRANSISTOR

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